



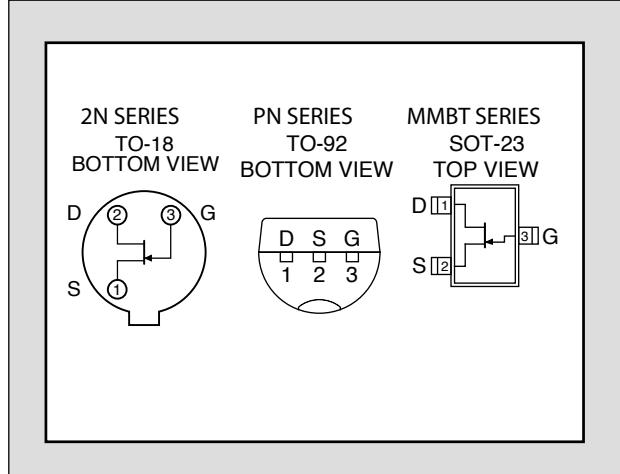
AMERICAN MICROSEMICONDUCTOR

2N3971/ PN4391,2,3 /MMBT4391

SERIES

SINGLE N-CHANNEL JFET SWITCH

FEATURES	
Replacement for Siliconix 2N3971 /PN/ 4391, 4392, & 4393	
LOW ON RESISTANCE	$r_{DS(on)} \leq 30\Omega$
FAST SWITCHING	$t_{ON} \leq 15\text{ns}$
ABSOLUTE MAXIMUM RATINGS ¹	
@ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature (2N3971)	-65 to 200° C
Storage Temperature (PN/MMBT)	-55 to 150° C
Junction Operating Temperature 2N3971	-55 to 200° C
Junction Operating Temperature (PN 4391,2,3)	-55 to 150° C
Maximum Power Dissipation	
Continuous Power Dissipation 2N3971	1800mW
Continuous Power Dissipation (PN/MMBT)	350mW
Maximum Currents	
Gate Current	50mA
Maximum Voltages	
Gate to Drain or Source 2N3971	-40V
Gate to Drain or Source (MMBT)	-35V



STATIC ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)

SYM.	CHARACTERISTIC	TYP	2N3971		PN4392		PN4393		UNIT	CONDITIONS
			MIN	MAX	MIN	MAX	MIN	MAX		
BV_{GSS}	Gate to Source Breakdown Voltage	2N3971	-40		-40		-40		V	$I_G = -1\mu A, V_{DS} = 0V$
		MMBT	-35		-35		-35			$V_{DS} = 20V, I_D = 1nA$
$V_{GS(\text{off})}$	Gate to Source Cutoff Voltage	2N3971	-2	-5	-2	-5	-0.5	-3	V	$V_{DS} = 15V, I_D = 10nA$
		MMBT	-4	-10	-2	-5	-0.5	-3		$I_G = 1mA, V_{DS} = 0V$
$V_{GS(F)}$	Gate to Source Forward Voltage	0.7		1		1		1		
$V_{DS(\text{on})}$	Drain to Source On Voltage	0.25						0.4	mA	$V_{GS} = 0V, I_D = 3mA$
		0.3				0.4				$V_{GS} = 0V, I_D = 6mA$
		0.35		0.4						$V_{GS} = 0V, I_D = 12mA$
$I_{DS S}$	Drain to Source Saturation Current ²	2N3971	25	75	25	75	5	30	mA	$V_{DS} = 20V, V_{GS} = 0V$
		PN	50	100	25	100	5	60		
		MMBT	50		25		5			
I_{GSS}	Gate Leakage Current	2N3971	-5		-100		-100		pA	$V_{GS} = -20V, V_{DS} = 0V$
		PN	-5		-1000		-1000			
I_G	Gate Operating Current	-5								$V_{DG} = 15V, I_D = 10mA$

STATIC ELECTRICAL CHARACTERISTICS CONT. @25 °C (unless otherwise stated)

SYM.	CHARACTERISTIC	TYP	2N3971		PN4392		PN4393		UNIT	CONDITIONS
			MIN	MAX	MIN	MAX	MIN	MAX		
$I_{D(\text{off})}$	Drain Cutoff Current	2N3941	5					100	pA	$V_{DS} = 20V, V_{GS} = -5V$
			5			100				$V_{DS} = 20V, V_{GS} = -7V$
			5	250						$V_{DS} = 20V, V_{GS} = -12V$
		PN4392,3	5					1000		$V_{DS} = 20V, V_{GS} = -5V$
			5			1000				$V_{DS} = 20V, V_{GS} = -7V$
			5	1000						$V_{DS} = 20V, V_{GS} = -12V$
		MMBT	5	100		100		100		$V_{DS} = 10V, V_{GS} = -10V$
$r_{DS(\text{on})}$	Drain to Source On Resistance			30		60		100	Ω	$V_{GS} = 0V, I_D = 1mA$

DYNAMIC ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)

SYM.	CHARACTERISTIC	TYP	2N3971		PN4392		PN4393		UNIT	CONDITIONS
			MIN	MAX	MIN	MAX	MIN	MAX		
g_{fs}	Forward Transconductance	6							mS	$V_{DS} = 20V, I_D = 1mA$ $f = 1kHz$
g_{os}	Output Conductance	25							μS	
$r_{ds(\text{on})}$	Drain to Source On Resistance			30		60		100	Ω	$V_{GS} = 0V, I_D = 0A$ $f = 1kHz$
C_{iss}	Input Capacitance	2N3971	12		14		14		pF	$V_{DS} = 20V, V_{GS} = 0V$ $f = 1MHz$
		PN	12		16		16			
		MMBT	13							
C_{rss}	Reverse Transfer Capacitance	2N3971	3.3					3.5	pF	$V_{DS} = 0V, V_{GS} = -5V$ $f = 1MHz$
		PN	3.5					5		
		MMBT	3.6							
		2N3971	3.2			3.5				
		PN	3.4			5			pF	$V_{DS} = 0V, V_{GS} = -7V$ $f = 1MHz$
		MMBT	3.5							
		2N3971	2.8	3.5						
		PN	3.0	5						$V_{DS} = 0V, V_{GS} = -12V$ $f = 1MHz$
e_n	Equivalent Input Noise Voltage	3							nV/\sqrt{Hz}	$V_{DS} = 10V, I_D = 10mA$ $f = 1kHz$

SWITCHING ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)

SYM.	CHARACTERISTIC	TYP	2N3971		4392		4393		UNIT	CONDITIONS	
			MIN	MAX	MIN	MAX	MIN	MAX			
$t_{d(on)}$	Turn On Time	2N/PN	2		15		15		ns	$V_{DD} = 10V, V_{GS(H)} = 0V$	
		MMBT	2								
t_r		2N/PN	2		5		5		ns		
		MMBT	2								
$t_{d(off)}$	Turn Off Time	2N/PN	6		20		35		ns		
		MMBT	6								
t_f		2N/PN	13		15		20				
		MMBT	13								

SWITCHING CIRCUIT CHARACTERISTICS

SYM.	4391	4392	4393
$V_{GS(L)}$	-12V	-7V	-5V
R_L	800Ω	1600Ω	3200Ω
$I_{D(on)}$	12mA	6mA	3mA

